

TABLE 14: NPN HIGH FREQUENCY

The devices shown in this table are designed for high frequency operation in such application areas as amplification, switching and oscillation.

Type	V_{CE0} V	Max. I_C mA	Max. $V_{CE(sat)}$ at			Min. f_T at		Max. Noise figure at			Max. C_{obo} at 1 MHz		RF P_O or RF P_G at mW	
			V	I_C mA	I_B mA	MHz	I_C mA	N dB	I_C μ A	f MHz	pF	V_{CB} V	or dB	f MHz
NPN														
ZTX327	30	400	1.0	100	20	800*	25	—	—	—	3.0	30	350mW	400
ZTX320	15	500	0.4	10	1.0	600	4	<6	1	60	1.7	10	15dB	200
ZTX321	15	500	0.4	3.0	0.3	600	4	<6	1	60	1.7	10	15dB	200
ZTX322	15	500	0.4	10	1.0	600	4	<6	1	60	1.7	10	15dB	200
ZTX323	15	500	0.4	10	1.0	600	4	<6	1	60	1.7	10	15dB	200
ZTX325	15	50	—	—	—	1000	2	5	2000	500	1.5	10	175mW	500

*Typical.

TABLE 15: NPN AVALANCHE TRANSISTOR

Specifically designed to operate in the avalanche mode. Suitable for pulsing laser diodes and other applications requiring very fast edges.

Type	V_{CBO} V	V_{CE0} V	h_{FE} at		Peak† Collector Current I_{CM} A	P_{tot} at $T_{amb} = 25^\circ C$ mW	I_{SB}^* at		f_T at	
			Min	I_C mA			A	V_C V	MHz	I_C mA
ZTX415	260	100	25	10	60	680	25	250	40	10

*Current in second breakdown. †Maximum pulse width 20n sec.